

ABSTRACT OF THE DISCLOSURE

A semiconductor device includes: a capacitor provided on a supporting substrate having an integrated circuit thereon and including a lower electrode, a dielectric film, and an upper electrode; a first interlayer insulating film provided so as to cover the capacitor; a first interconnect selectively provided on the first interlayer insulating film and electrically connected to the integrated circuit and the capacitor through a first contact hole formed in the first interlayer insulating film; a second interlayer insulating film formed of ozone TEOS and provided so as to cover the first interconnect; a second interconnect selectively provided on the second interlayer insulating film and electrically connected to the first interconnect through a second contact hole formed in the second interlayer insulating film; and a passivation layer provided so as to cover the second interconnect.